

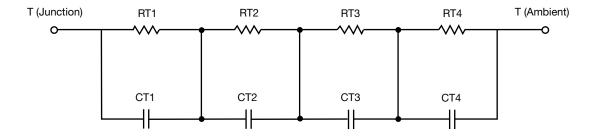
# **R-C Thermal Model Parameters**

## **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

# **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION  THERMAL RESISTANCE (°C/W)					
RT1	n/a	200.8993m	n/a		
RT2	n/a	36.7038m	n/a		
RT3	n/a	105.3080m	n/a		
RT4	n/a	157.0889m	n/a		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	190.6285m	n/a		
CT2	n/a	1.0648	n/a		
CT3	n/a	52.8195m	n/a		
CT4	n/a	6.5860m	n/a		

#### Note

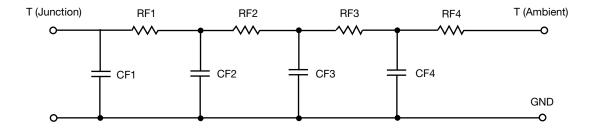
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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# **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION					
THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	n/a	234.5270m	n/a		
RF2	n/a	95.1208m	n/a		
RF3	n/a	137.1796m	n/a		
RF4	n/a	33.1726m	n/a		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	6.1254m	n/a		
CF2	n/a	70.1306m	n/a		
CF3	n/a	104.8455m	n/a		
CF4	n/a	16.4391m	n/a		

### Note

• n/a indicates not applicable





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